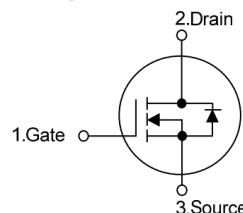


4A, 650V N-CHANNEL POWER MOSFET

Features

- $R_{DS(on)}=2.92\Omega$ (Max.) @ $V_{GS}=10V, I_D=2A$
- Low gate charge
- Low Ciss
- Fast switching



Applications

- LED Power Supplies
- Cell Phone Charger
- Standby Power

Key Performance and Package Parameters

Order codes	V_{DS}	I_D	$R_{DS(ON)}$, Typ	T_{vjmax}	Marking	Package
XD004M065BX1H3	650V	4A	1.72Ω	150°C	D04M65BX1H3	TO220F-3L
XD004M065BX1G3	650V	4A	1.72Ω	150°C	D04M65BX1G3	TO252-2L

Absolute Maximum Ratings ($T_c= 25^\circ C$ unless otherwise noted.)

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	650	V
V_{GSS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current ($T_c=25^\circ C$)	4	A
	Continuous Drain Current ($T_c=100^\circ C$)	2	A
I_{DM}	Pulsed Drain Current	16	A
P_D	Maximum Power Dissipation ($T_c=25^\circ C$, For TO252-2L)	75	W
	Maximum Power Dissipation ($T_c=100^\circ C$, For TO252-2L)	30	W
E_{AS}	Avalanche Energy, Single pulse($L=10mH$) (note1)	58	mJ
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Conditoins	Max.	Units
$R_{\theta JC}$	Thermal Resistance-Junction to case (Steady State)	TO220F-3L	4.5	°C/W
		TO252-2L	1.67	°C/W

Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0\text{V}$, $I_{\text{DS}} = 250\mu\text{A}$	650	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 650\text{V}$, $V_{\text{GS}} = 0\text{V}$	---	---	1	μA
I_{GSS}	Gate Leakage Current, Forward	$V_{\text{GS}} = 30\text{V}$, $V_{\text{DS}} = 0\text{V}$	---	---	100	nA
	Gate Leakage Current, Reverse	$V_{\text{GS}} = -30\text{V}$, $V_{\text{DS}} = 0\text{V}$	---	---	-100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{DS}} = 250\mu\text{A}$	2	2.88	4	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-state Resistance	$V_{\text{GS}} = 10\text{V}$, $I_{\text{DS}} = 2\text{A}$	--	2.31	2.92	Ω
Q_g	Total Gate Charge	$V_{\text{DS}} = 520\text{V}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{DS}} = 4\text{A}$	---	12.8	---	nC
Q_{gs}	Gate-Source Charge		---	5.8	---	nC
Q_{gd}	Gate-Drain Charge		---	2.8	---	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}} = 325\text{V}$, $V_{\text{GE}} = 10\text{V}$ $I_{\text{DS}} = 4\text{A}$, $R_{\text{G}} = 10\Omega$	---	10.4	---	nS
t_r	Turn-on Rise Time		--	4	--	nS
$t_{\text{d}(\text{off})}$	Turn-off Delay Time			21.6	---	nS
t_f	Turn-off Fall Time		---	4	---	nS
C_{iss}	Input Capacitance	$V_{\text{DS}} = 25\text{V}$ $V_{\text{GS}} = 0\text{V}$ $f = 1\text{MHz}$	---	584	---	pF
C_{oss}	Output Capacitance		---	37	---	pF
C_{rss}	Reverse Transfer Capacitance		---	27	---	pF

Diode Characteristics of Diode ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V_{SD}	Diode Forward Voltage	$I_{\text{SD}} = 2\text{A}$, $V_{\text{GS}} = 0\text{V}$	---	---	1.2	V
t_{rr}	Diode Reverse Recovery Time	$V_{\text{DS}} = 30\text{V}$, $I_{\text{SD}} = 1\text{A}$, $dI_{\text{SD}}/dt = 100\text{A}/\mu\text{s}$	---	125	---	ns
Q_{rr}	Diode Reverse Recovery Charge		---	262	---	nC

Notes:

- 1.
- $L = 10\text{mH}$
- ,
- $I_{\text{AS}} = 3.4\text{A}$
- ,
- $V_{\text{DD}} = 50\text{V}$
- ,
- $R_{\text{G}} = 25\Omega$
- , Starting
- $T_J = 25^\circ\text{C}$
- .

Typical Characteristics

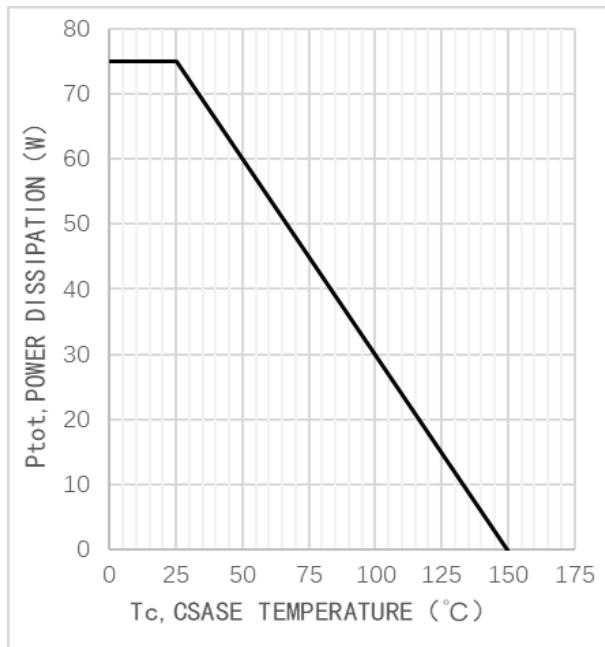


Fig.1 Power Dissipation(For TO252-2L)

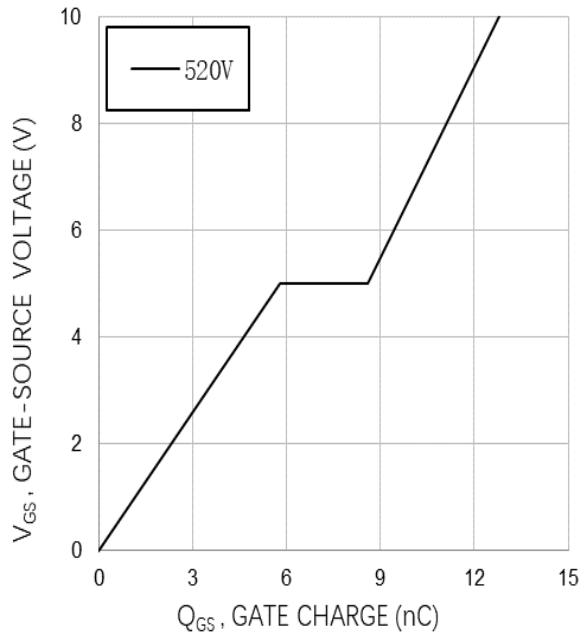


Fig.2 Gate Charge

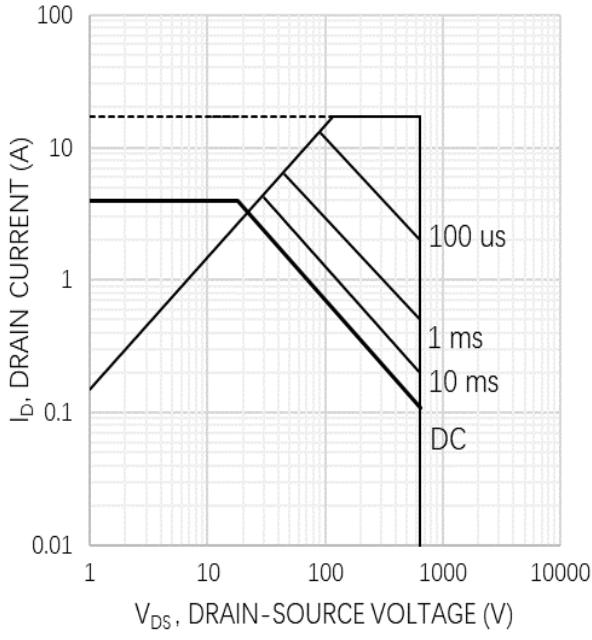


Fig.3 Safe Operation Area

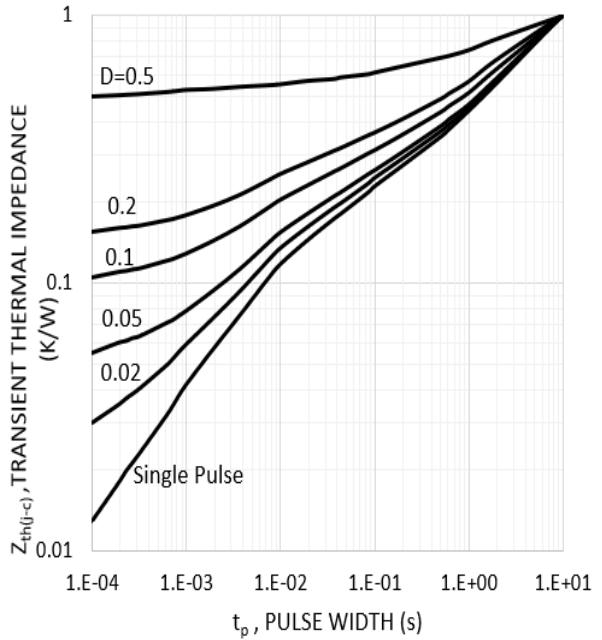


Fig.4 Thermal Transient Impedance

Typical Characteristics

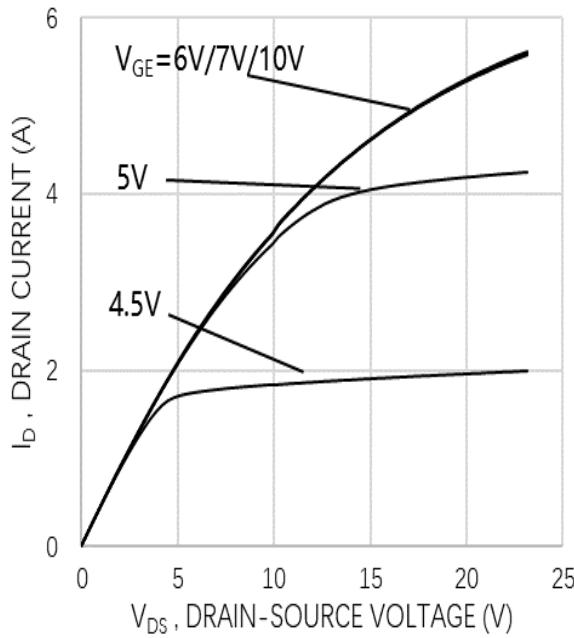


Fig.5 Output Characteristics

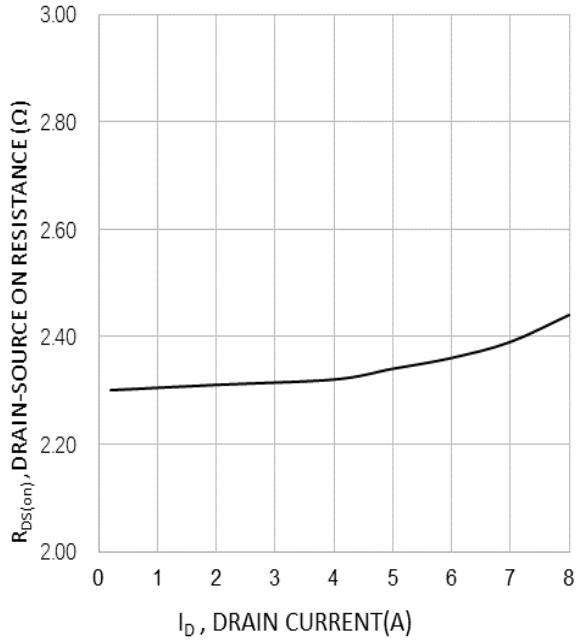


Fig.6 Drain-Source On Resistance

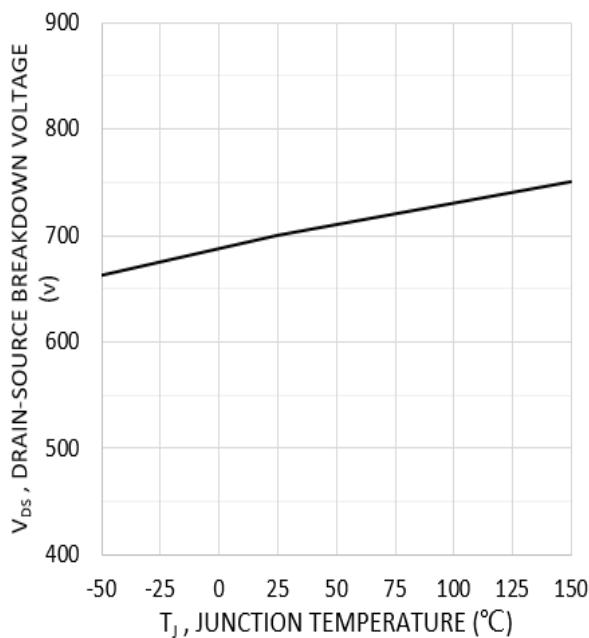


Fig.7 Drain-Source Breakdown Voltage

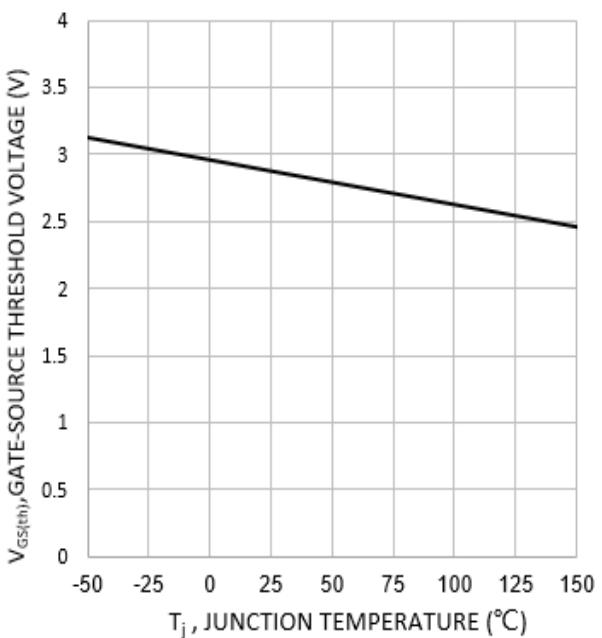


Fig.8 Gate Threshold Voltage

Typical Characteristics

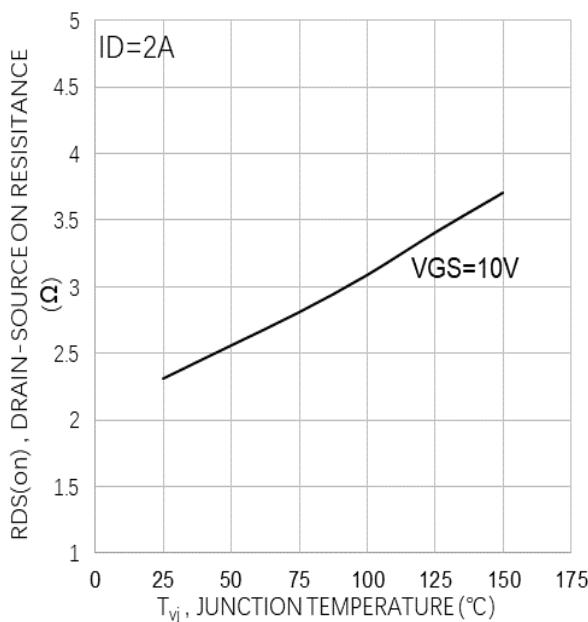


Fig.9 Drain-Source On Resistance

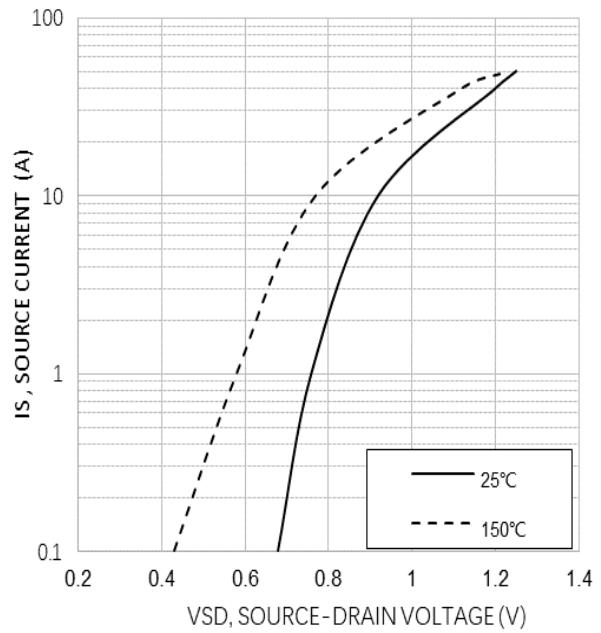


Fig.10 Source-Drain Diode Forward

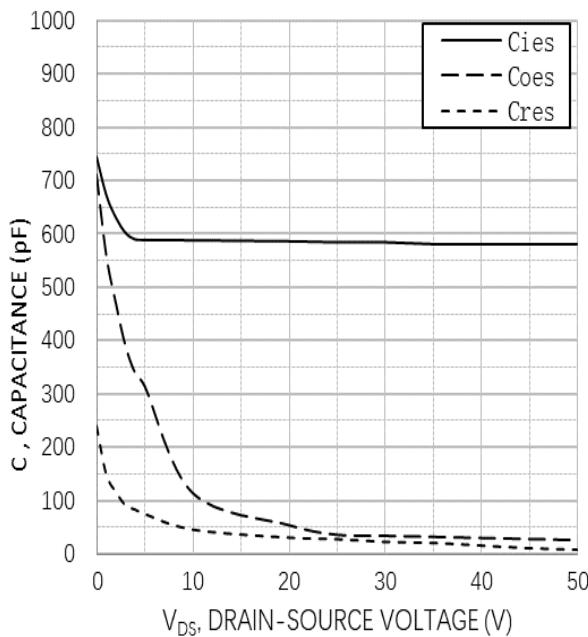
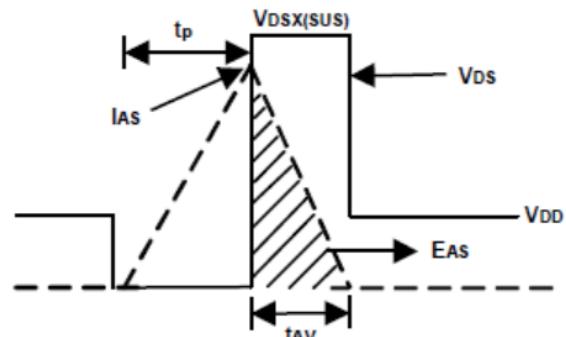
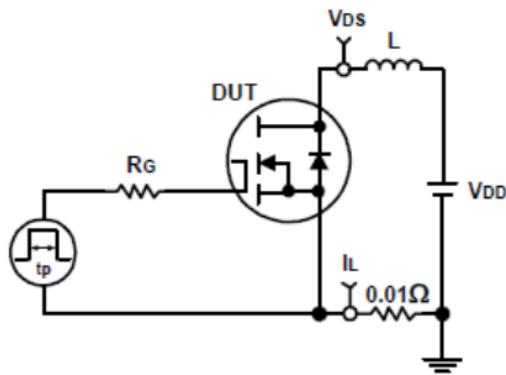
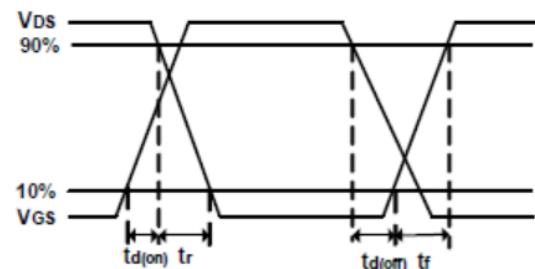
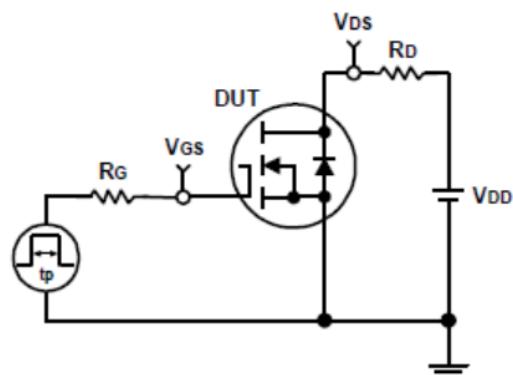


Fig.11 Capacitance

Avalanche Test Circuit and Waveforms

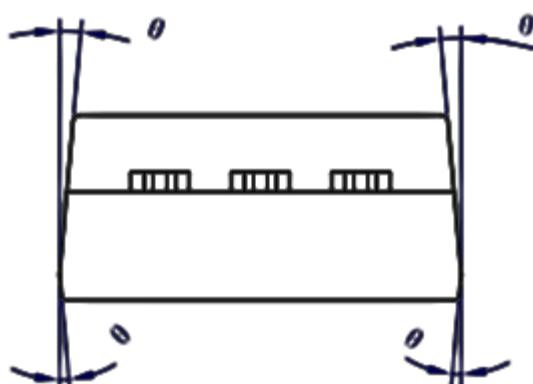
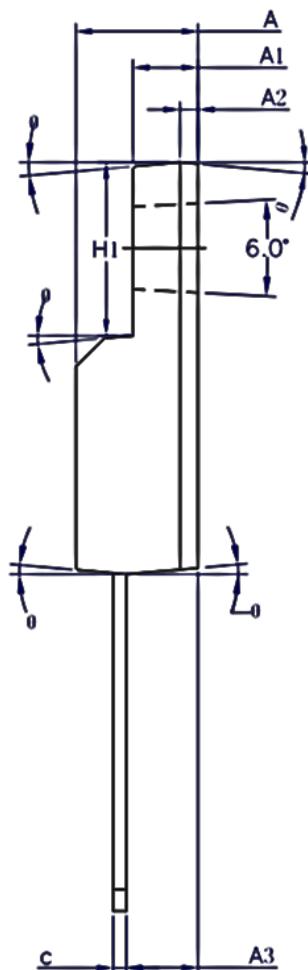
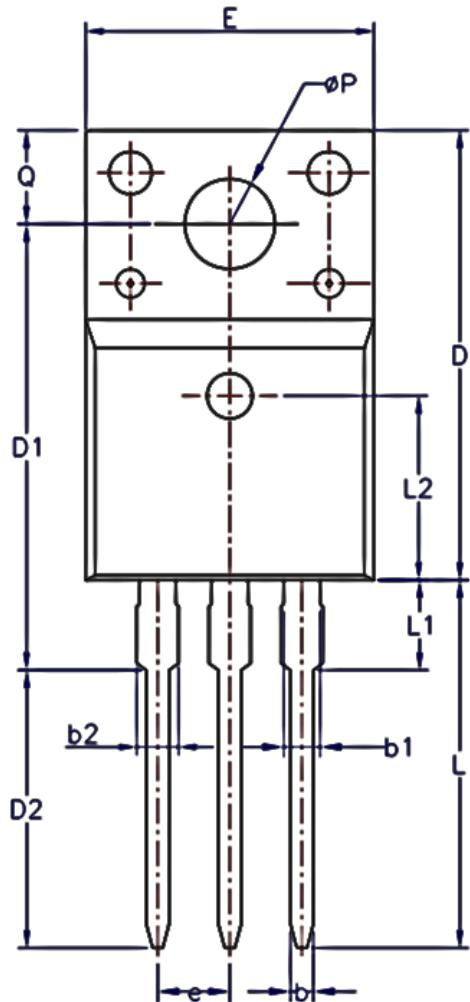


Switching Time Test Circuit and Waveforms



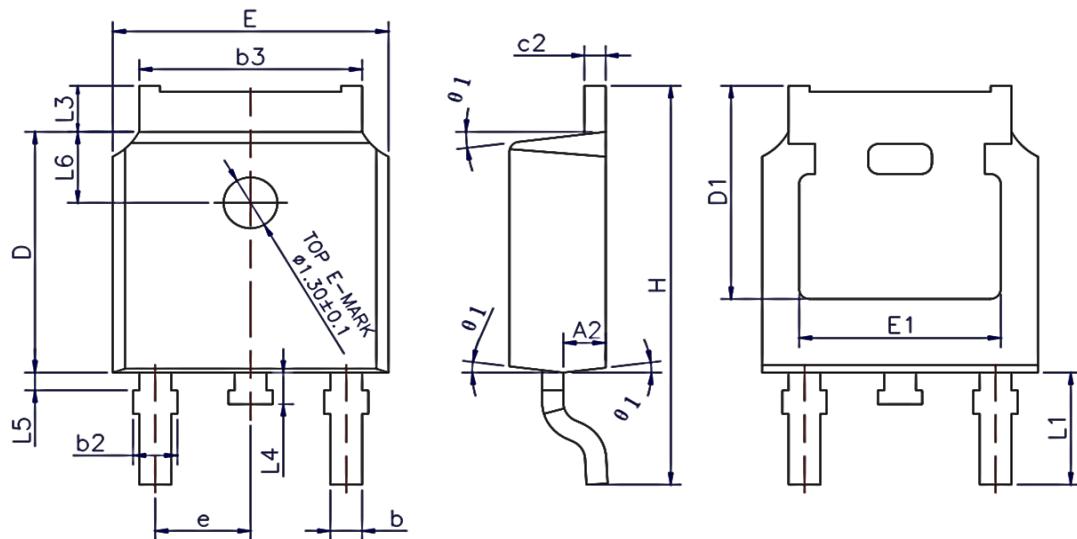
Package Information

TO-220F-3L



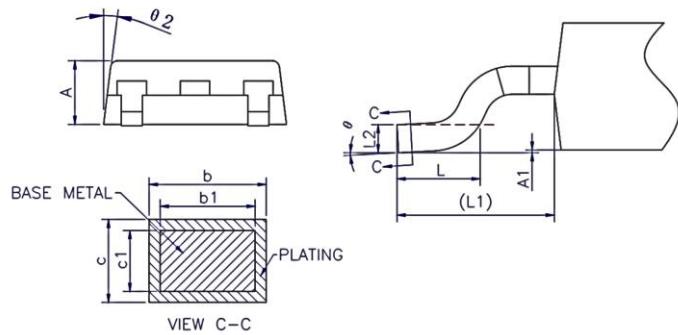
SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.93
b	0.70	—	0.90
b1	1.18	—	1.38
b2	—	—	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.0
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	—	—	3.50
L2	6.50REF		
øP	3.08	3.18	3.28
Q	3.20	—	3.40
θ 1	1°	3°	5°

TO-252-2L



COMMON DIMENSIONS
 (UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0	---	0.10
A2	0.90	1.01	1.10
b	0.72	---	0.85
b1	0.71	0.76	0.81
b2	0.72	---	0.90
b3	5.13	5.33	5.46
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	0.47	---	0.60
D	6.00	6.10	6.20
D1	5.25	---	---
E	6.50	6.60	6.70
E1	4.70	---	---
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.508 BSC		
L3	0.90	---	1.25
L4	0.60	0.80	1.00
L5	0.15	---	0.75
L6	1.80 REF		
θ	0°	---	8°
θ1	5°	7°	9°
θ2	5°	7°	9°


NOTES:

ALL DIMENSIONS REFER TO JEDEC STANDARD
 TO-252 AA DO NOT INCLUDE MOLD FLASH OR
 PROTRUSIONS

Revision History

Ver.	Date	Change Notice
1.0	2022/05/20	Release